



Welcome to [E-XFL.COM](#)

### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	8052
Core Size	8-Bit
Speed	40MHz
Connectivity	EBI/EMI, UART/USART
Peripherals	POR
Number of I/O	36
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Surface Mount
Package / Case	44-BQFP
Supplier Device Package	-
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nuvoton-technology-corporation-america/w78e516b40fl">https://www.e-xfl.com/product-detail/nuvoton-technology-corporation-america/w78e516b40fl</a>



8.4	Port Access Cycle.....	27
9.	TYPICAL APPLICATION CIRCUITS .....	28
9.1	External Program Memory and Crystal .....	28
9.2	Expanded External Data Memory and Oscillator .....	29
10.	PACKAGE DIMENSIONS .....	30
10.1	40-pin DIP .....	30
10.2	44-pin PLCC .....	30
10.3	44-pin PQFP .....	31
11.	APPLICATION NOTE .....	32
11.1	In-system Programming Software Examples .....	32
12.	REVISION HISTORY .....	37



### **5.3 Clock**

The W78E516B is designed with either a crystal oscillator or an external clock. Internally, the clock is divided by two before it is used by default. This makes the W78E516B relatively insensitive to duty cycle variations in the clock.

### **5.4 Crystal Oscillator**

The W78E516B incorporates a built-in crystal oscillator. To make the oscillator work, a crystal must be connected across pins XTAL1 and XTAL2. In addition, a load capacitor must be connected from each pin to ground, and a resistor must also be connected from XTAL1 to XTAL2 to provide a DC bias when the crystal frequency is above 24 MHz.

### **5.5 External Clock**

An external clock should be connected to pin XTAL1. Pin XTAL2 should be left unconnected. The XTAL1 input is a CMOS-type input, as required by the crystal oscillator. As a result, the external clock signal should have an input one level of greater than 3.5 volts.

### **5.6 Power Management**

#### **Idle Mode**

Setting the IDL bit in the PCON register enters the idle mode. In the idle mode, the internal clock to the processor is stopped. The peripherals and the interrupt logic continue to be clocked. The processor will exit idle mode when either an interrupt or a reset occurs.

#### **Power-down Mode**

When the PD bit in the PCON register is set, the processor enters the power-down mode. In this mode all of the clocks are stopped, including the oscillator. To exit from power-down mode is by a hardware reset or external interrupts  $\overline{\text{INT0}}$  to  $\overline{\text{INT1}}$  when enabled and set to level triggered.

### **5.7 Reduce EMI Emission**

The W78E516B allows user to diminish the gain of on-chip oscillator amplifier by using programmer to clear the B7 bit of security register. Once B7 is set to 0, a half of gain will be decreased. Care must be taken if user attempts to diminish the gain of oscillator amplifier, reducing a half of gain may affect the external crystal operating improperly at high frequency above 24 MHz. The value of R and C1, C2 may need some adjustment while running at lower gain.

### **5.8 Reset**

The external RESET signal is sampled at S5P2. To take effect, it must be held high for at least two machine cycles while the oscillator is running. An internal trigger circuit in the reset line is used to deglitch the reset line when the W78E516B is used with an external RC network. The reset logic also has a special glitch removal circuit that ignores glitches on the reset line. During reset, the ports are initialized to FFH, the stack pointer to 07H, PCON (with the exception of bit 4) to 00H, and all of the other SFR registers except SBUF to 00H. SBUF is not reset.



## W78E516B Special Function Registers (SFRs) and Reset Values

F8									FF
F0	+B 00000000						CHPENR 00000000		F7
E8									EF
E0	+ACC 00000000								E7
D8	+P4 xxxx1111								DF
D0	+PSW 00000000								D7
C8	+T2CON 00000000		RCAP2L 00000000	RCAP2H 00000000	TL2 00000000	TH2 00000000			CF
C0	XICON 00000000		<b>P4CONA</b> 00000000	<b>P4CONB</b> 00000000	<b>SFRAL</b> 00000000	<b>SFRAH</b> 00000000	<b>SFRFD</b> 00000000	<b>SFRCN</b> 00000000	C7
B8	+IP 00000000							<b>CHPCON</b> 0xx00000	BF
B0	+P3 00000000				<b>P43AL</b> 00000000	<b>P43AH</b> 00000000			B7
A8	+IE 00000000				<b>P42AL</b> 00000000	<b>P42AH</b> 00000000	<b>P2ECON</b> 0000XX00		AF
A0	+P2 11111111								A7
98	+SCON 00000000	SBUF xxxxxxxx					<b>P2EAL</b> 00000000	<b>P2EAH</b> 00000000	9F
90	+P1 11111111				<b>P41AL</b> 00000000	<b>P41AH</b> 00000000			97
88	+TCON 00000000	TMOD 00000000	TL0 00000000	TL1 00000000	TH0 00000000	TH1 00000000			8F
80	+P0 11111111	SP 00000111	DPL 00000000	DPH 00000000	<b>P40AL</b> 00000000	<b>P40AH</b> 00000000		PCON 00110000	87

## Notes:

1. The SFRs marked with a plus sign(+) are both byte- and bit-addressable.
2. The text of SFR with bold type characters are extension function registers.

**P2ECON (AEH)**

BIT	NAME	FUNCTION
7	P43CSINV	The active polarity of P4.3 when pin P4.3 is defined as read and/or write strobe signal. = 1: P4.3 is active high when pin P4.3 is defined as read and/or write strobe signal. = 0: P4.3 is active low when pin P4.3 is defined as read and/or write strobe signal.
6	P42CSINV	The similarity definition as P43SINV.
5	P41CSINV	The similarity definition as P43SINV.
5	P41CSINV	The similarity definition as P43SINV.
4	P40CSINV	The similarity definition as P43SINV.
3	-	Reserve
2	-	Reserve
1	-	0
0	-	0

**5.11 Port 4 Base Address Registers****P40AH, P40AL:**

The Base address register for comparator of P4.0. P40AH contains the high-order byte of address, P40AL contains the low-order byte of address.

**P41AH, P41AL:**

The Base address register for comparator of P4.1. P41AH contains the high-order byte of address, P41AL contains the low-order byte of address.

**P42AH, P42AL:**

The Base address register for comparator of P4.2. P42AH contains the high-order byte of address, P42AL contains the low-order byte of address.

**P43AH, P43AL:**

The Base address register for comparator of P4.3. P43AH contains the high-order byte of address, P43AL contains the low-order byte of address.

**P4 (D8H)**

BIT	NAME	FUNCTION
7	-	Reserve
6	-	Reserve
5	-	Reserve
4	-	Reserve
3	P43	Port 4 Data bit which outputs to pin P4.3 at mode 0.
2	P42	Port 4 Data bit which outputs to pin P4.2 at mode 0.
1	P41	Port 4 Data bit which outputs to pin P4.1 at mode 0.
0	P40	Port 4 Data bit which outputs to pin P4.0 at mode 0.

Here is an example to program the P4.0 as a write strobe signal at the I/O port address 1234H – 1237H and positive polarity, and P4.1 – P4.3 are used as general I/O ports.

```
MOV P40AH, #12H
```

```
MOV P40AL, #34H ; Base I/O address 1234H for P4.0
```

```
MOV P4CONA, #00001010B ; P4.0 a write strobe signal and address line A0 and A1 are masked.
```

```
MOV P4CONB, #00H ; P4.1 – P4.3 as general I/O port which are the same as PORT1
```

```
MOV P2ECON, #10H ; Write the P40SINV = 1 to inverse the P4.0 write strobe polarity  
; default is negative.
```

Then any instruction MOVX @DPTR, A (with DPTR = 1234H – 1237H) will generate the positive polarity write strobe signal at pin P4.0. And the instruction MOV P4, #XX will output the bit3 to bit1 of data #XX to pin P4.3 – P4.1.



**SFRAH, SFRAL:** The objective address of on-chip Flash EPROM in the in-system programming mode. SFRFAH contains the high-order byte of address, SFRFAL contains the low-order byte of address.

**SFRFD:** The programming data for on-chip Flash EPROM in programming mode.

**SFRCN:** The control byte of on-chip Flash EPROM programming mode.

#### SFRCN (C7)

BIT	NAME	FUNCTION
7	-	Reserve.
6	WFWIN	On-chip Flash EPROM bank select for in-system programming. = 0: 64K bytes Flash EPROM bank is selected as destination for re-programming. = 1: 4K bytes Flash EPROM bank is selected as destination for re-programming.
5	OEN	Flash EPROM output enable.
4	CEN	Flash EPROM chip enable.
3, 2, 1, 0	CTRL[3:0]	The flash control signals

MODE	WFWIN	CTRL<3:0>	OEN	CEN	SFRAH, SFRAL	SFRFD
Erase 64KB APROM	0	0010	1	0	X	X
Program 64KB APROM	0	0001	1	0	Address in	Data in
Read 64KB APROM	0	0000	0	0	Address in	Data out
Erase 4KB LDROM	1	0010	1	0	X	X
Program 4KB LDROM	1	0001	1	0	Address in	Data in
Read 4KB LDROM	1	0000	0	0	Address in	Data out



### 5.13 In-System Programming Control Register (CHPCON)

#### CHPCON (BFH)

BIT	NAME	FUNCTION
7	SWRESET (F04KMODE)	When this bit is set to 1, and both FBOOTSL and FPROGEN are set to 1. It will enforce microcontroller reset to initial condition just like power on reset. This action will re-boot the microcontroller and start to normal operation. To read this bit in logic-1 can determine that the F04KBOOT mode is running.
6	-	Reserve.
5	-	Reserve.
4	ENAXRAM	1: Enable on-chip AUX-RAM. 0: Disable the on-chip AUX-RAM
3	0	Must set to 0.
2	0	Must set to 0.
1	FBOOTSL	The Program Location Select. 0: The Loader Program locates at the 64 KB APROM. 4KB LDROM is destination for re-programming. 1: The Loader Program locates at the 4 KB memory bank. 64KB APROM is destination for re-programming.
0	FPROGEN	FLASH EPROM Programming Enable. = 1: enable. The microcontroller enter the in-system programming mode after entering the idle mode and wake-up from interrupt. During in-system programming mode, the operation of erase, program and read are achieve when device enters idle mode. = 0: disable. The on-chip flash memory is read-only. In-system programmability is disabled.

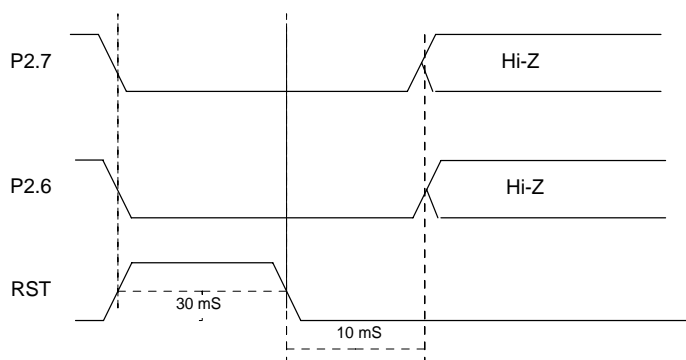
#### F04KBOOT Mode (Boot from LDROM)

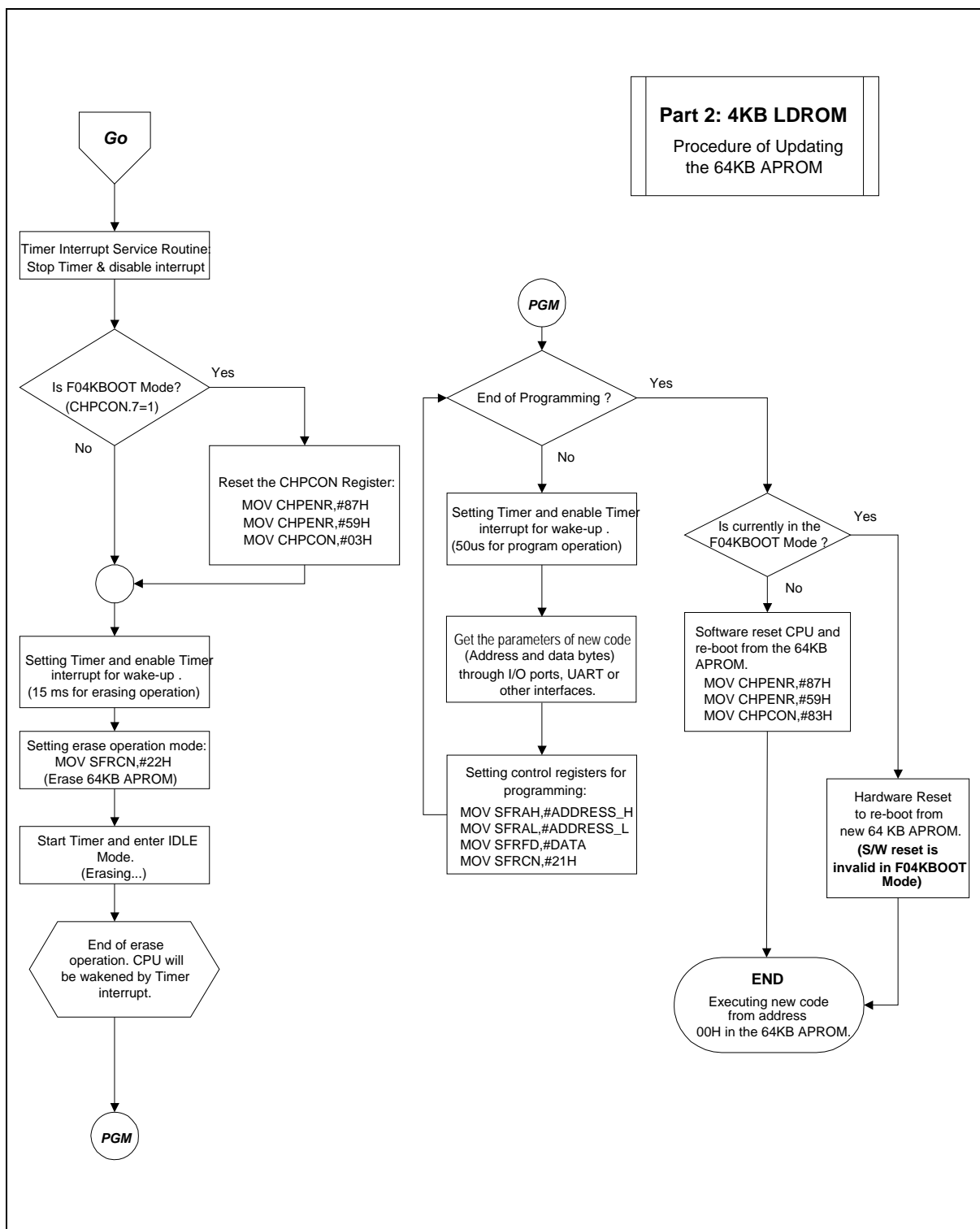
By default, the W78E516B boots from APROM program after a power on reset. On some occasions, user can force the W78E516B to boot from the LDROM program via following settings. The possible situation that you need to enter F04KBOOT mode when the APROM program can not run properly and device can not jump back to LDROM to execute in-system programming function. Then you can use this F04KBOOT mode to force the W78E516B jumps to LDROM and executes in-system programming procedure. When you design your system, you may reserve the pins P2.6, P2.7 to switches or jumpers. For example in a CD-ROM system, you can connect the P2.6 and P2.7 to PLAY and EJECT buttons on the panel. When the APROM program fails to execute the normal application program. User can press both two buttons at the same time and then turn on the power of the personal computer to force the W78E516B to enter the F04KBOOT mode. After power on of personal computer, you can release both buttons and finish the in-system programming procedure to update the APROM code. In application system design, user must take care of the P2, P3, ALE,  $\overline{\text{EA}}$  and  $\overline{\text{PSEN}}$  pin value at reset to prevent from accidentally activating the programming mode or F04KBOOT mode.

**F04KBOOT MODE**

P4.3	P2.7	P2.6	MODE
X	L	L	F04KBOOT
L	X	X	F04KBOOT

**The Reset Timing For Entering  
F04KBOOT Mode**



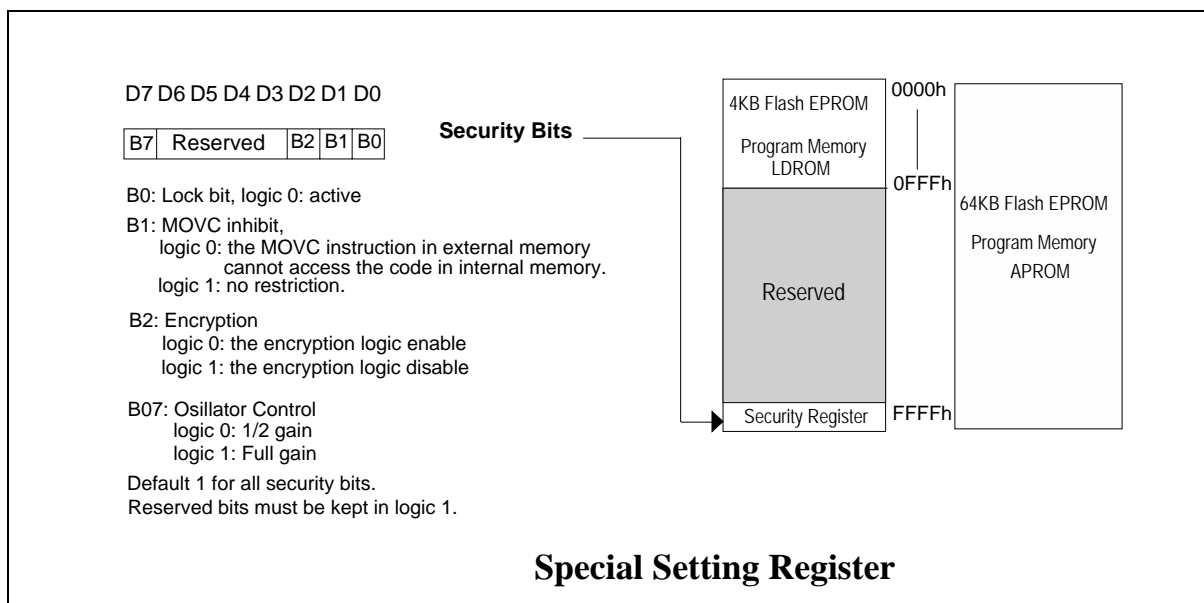




## 6. SECURITY

During the on-chip Flash EPROM programming mode, the Flash EPROM can be programmed and verified repeatedly. Until the code inside the Flash EPROM is confirmed OK, the code can be protected. The protection of Flash EPROM and those operations on it are described below.

The W78E516B has a Special Setting Register, the Security Register, which can not be accessed in programming mode. Those bits of the Security Register can not be changed once they have been programmed from high to low. They can only be reset through erase-all operation. The Security Register is located at the 0FFFFh of the LDROM space.



### 6.1 Lock Bit

This bit is used to protect the customer's program code in the W78E516B. It may be set after the programmer finishes the programming and verifies sequence. Once this bit is set to logic 0, both the Flash EPROM data and Special Setting Registers can not be accessed again.

### 6.2 MOVC Inhibit

This bit is used to restrict the accessible region of the MOVC instruction. It can prevent the MOVC instruction in external program memory from reading the internal program code. When this bit is set to logic 0, a MOVC instruction in external program memory space will be able to access code only in the external memory, not in the internal memory. A MOVC instruction in internal program memory space will always be able to access the ROM data in both internal and external memory. If this bit is logic 1, there are no restrictions on the MOVC instruction.



## 7. ELECTRICAL CHARACTERISTICS

### 7.1 Absolute Maximum Ratings

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
DC Power Supply	V <sub>DD</sub> – V <sub>SS</sub>	-0.3	+6.0	V
Input Voltage	V <sub>IN</sub>	V <sub>SS</sub> -0.3	V <sub>DD</sub> +0.3	V
Operating Temperature	T <sub>A</sub>	0	70	°C
Storage Temperature	T <sub>ST</sub>	-55	+150	°C

**Note:** Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

### 7.2 D.C. Characteristics

(V<sub>DD</sub> – V<sub>SS</sub> = 5V ±10%, T<sub>A</sub> = 25°C, F<sub>osc</sub> = 20 MHz, unless otherwise specified.)

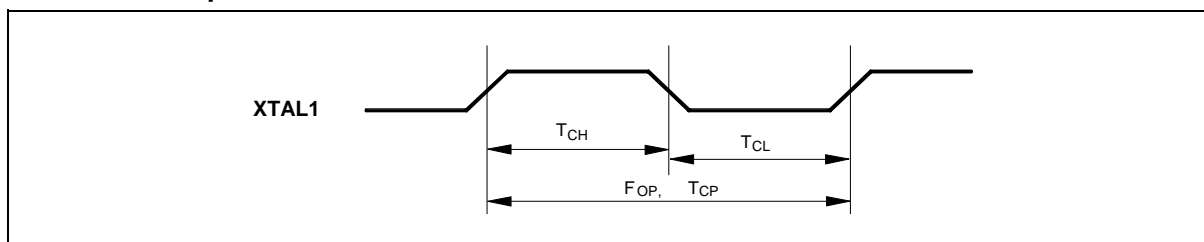
PARAMETER	SYM.	SPECIFICATION			TEST CONDITIONS
		MIN.	MAX.	UNIT	
Operating Voltage	V <sub>DD</sub>	4.5	5.5	V	RST = 1, P0 = V <sub>DD</sub>
Operating Current	I <sub>DD</sub>	-	20	mA	No load V <sub>DD</sub> = 5.5V
Idle Current	I <sub>IDLE</sub>	-	6	mA	Idle mode V <sub>DD</sub> = 5.5V
Power Down Current	I <sub>PWDN</sub>	-	50	μA	Power-down mode V <sub>DD</sub> = 5.5V
Input Current P1, P2, P3, P4	I <sub>IN1</sub>	-50	+10	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 0V or V <sub>DD</sub>
Input Current RST	I <sub>IN2</sub>	-10	+300	μA	V <sub>DD</sub> = 5.5V 0 < V <sub>IN</sub> < V <sub>DD</sub>
Input Leakage Current P0, $\overline{EA}$	I <sub>LK</sub>	-10	+10	μA	V <sub>DD</sub> = 5.5V 0V < V <sub>IN</sub> < V <sub>DD</sub>
Logic 1 to 0 Transition Current P1, P2, P3, P4	I <sub>TL</sub> <sup>[*4]</sup>	-500	-	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 2.0V
Input Low Voltage P0, P1, P2, P3, P4, $\overline{EA}$	V <sub>IL1</sub>	0	0.8	V	V <sub>DD</sub> = 4.5V
Input Low Voltage RST	V <sub>IL2</sub>	0	0.8	V	V <sub>DD</sub> = 4.5V
Input Low Voltage XTAL1 <sup>[*4]</sup>	V <sub>IL3</sub>	0	0.8	V	V <sub>DD</sub> = 4.5V



### 7.3 A.C. Characteristics

The AC specifications are a function of the particular process used to manufacture the part, the ratings of the I/O buffers, the capacitive load, and the internal routing capacitance. Most of the specifications can be expressed in terms of multiple input clock periods (TCP), and actual parts will usually experience less than a  $\pm 20$  nS variation. The numbers below represent the performance expected from a 0.6 micron CMOS process when using 2 and 4 mA output buffers.

#### 7.3.1 Clock Input Waveform



PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTES
Operating Speed	Fop	0	-	40	MHz	1
Clock Period	TCP	25	-	-	nS	2
Clock High	Tch	10	-	-	nS	3
Clock Low	Tcl	10	-	-	nS	3

**Notes:**

1. The clock may be stopped indefinitely in either state.
2. The TCP specification is used as a reference in other specifications.
3. There are no duty cycle requirements on the XTAL1 input.

#### 7.3.2 Program Fetch Cycle

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTES
Address Valid to ALE Low	TAAS	1 TCP- $\Delta$	-	-	nS	4
Address Hold from ALE Low	TAAH	1 TCP- $\Delta$	-	-	nS	1, 4
ALE Low to $\overline{\text{PSEN}}$ Low	TAPL	1 TCP- $\Delta$	-	-	nS	4
$\overline{\text{PSEN}}$ Low to Data Valid	TPDA	-	-	2 TCP	nS	2
Data Hold after $\overline{\text{PSEN}}$ High	TPDH	0	-	1 TCP	nS	3
Data Float after $\overline{\text{PSEN}}$ High	TPDZ	0	-	1 TCP	nS	
ALE Pulse Width	TALW	2 TCP- $\Delta$	2 TCP	-	nS	4
$\overline{\text{PSEN}}$ Pulse Width	TPSW	3 TCP- $\Delta$	3 TCP	-	nS	4

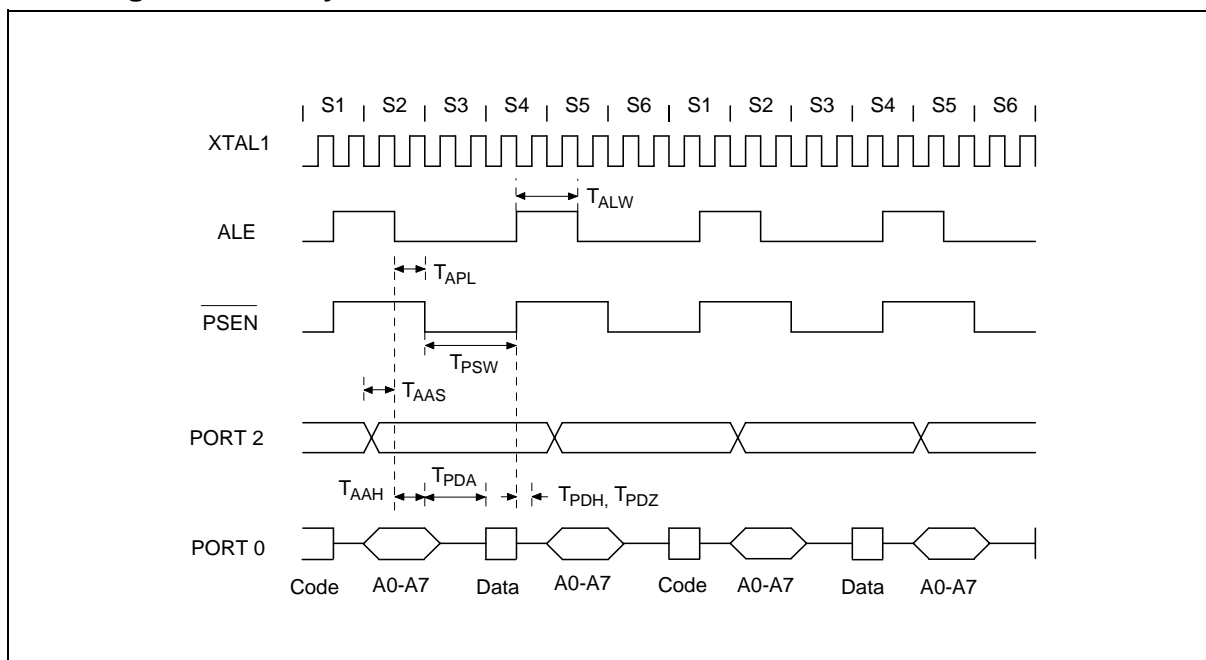
**Notes:**

1. P0.0 – P0.7, P2.0 – P2.7 remain stable throughout entire memory cycle.
2. Memory access time is 3 TCP.
3. Data have been latched internally prior to  $\overline{\text{PSEN}}$  going high.
4. " $\Delta$ " (due to buffer driving delay and wire loading) is 20 nS.

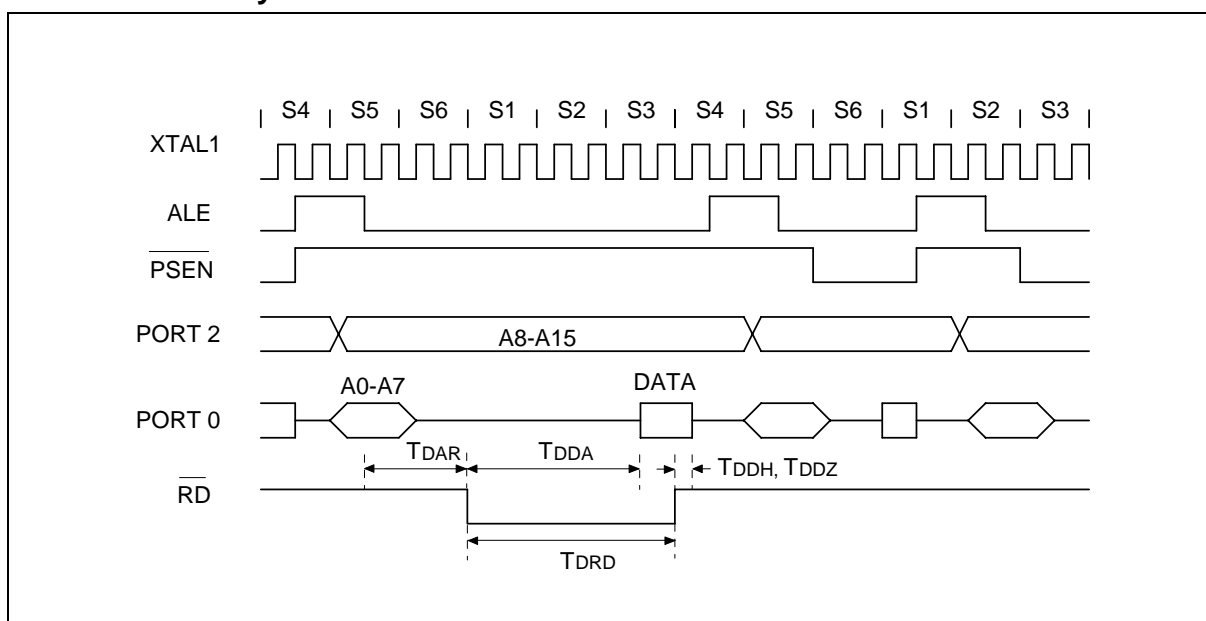


## 8. TIMING WAVEFORMS

### 8.1 Program Fetch Cycle



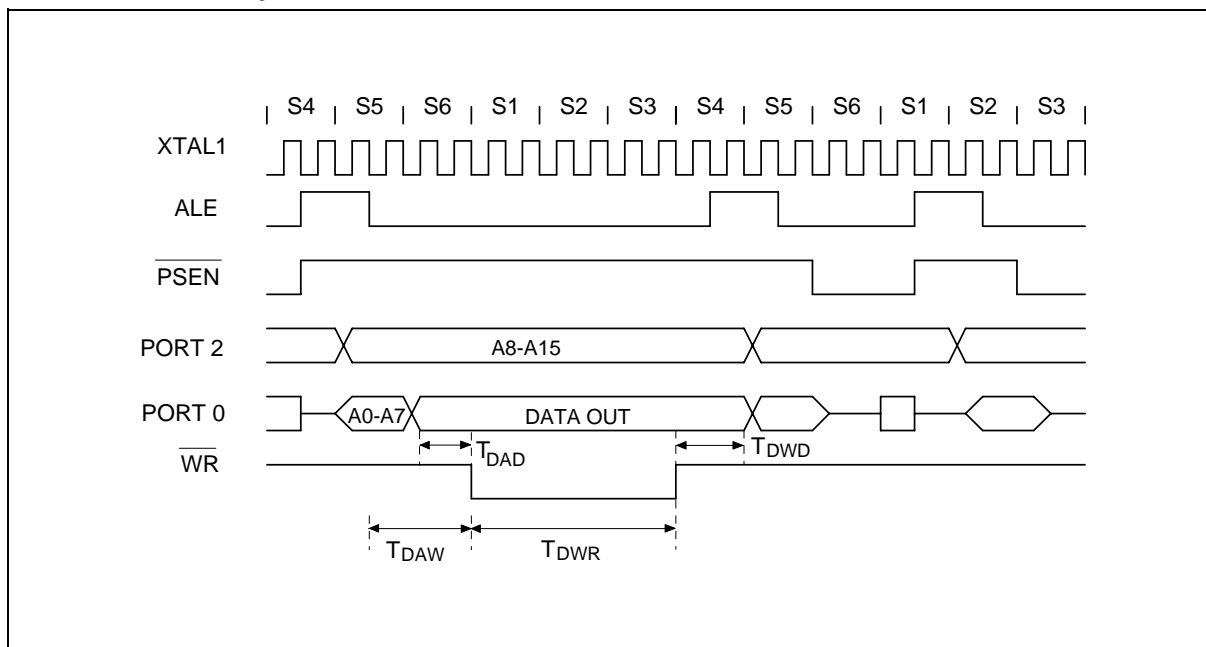
### 8.2 Data Read Cycle



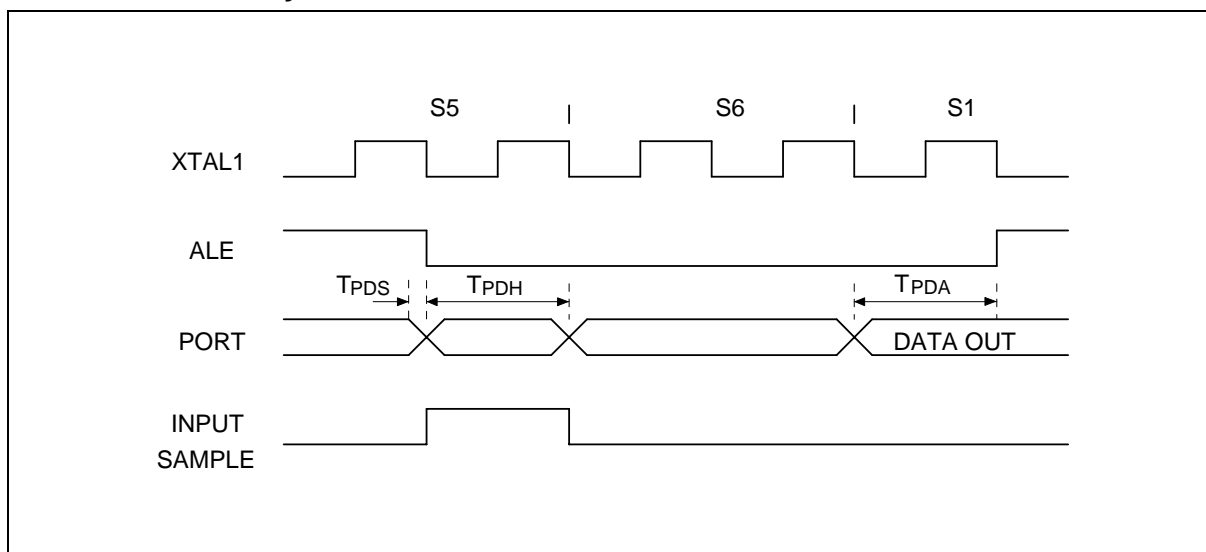


Timing Waveforms, continued

### 8.3 Data Write Cycle



### 8.4 Port Access Cycle





## 9. TYPICAL APPLICATION CIRCUITS

### 9.1 External Program Memory and Crystal

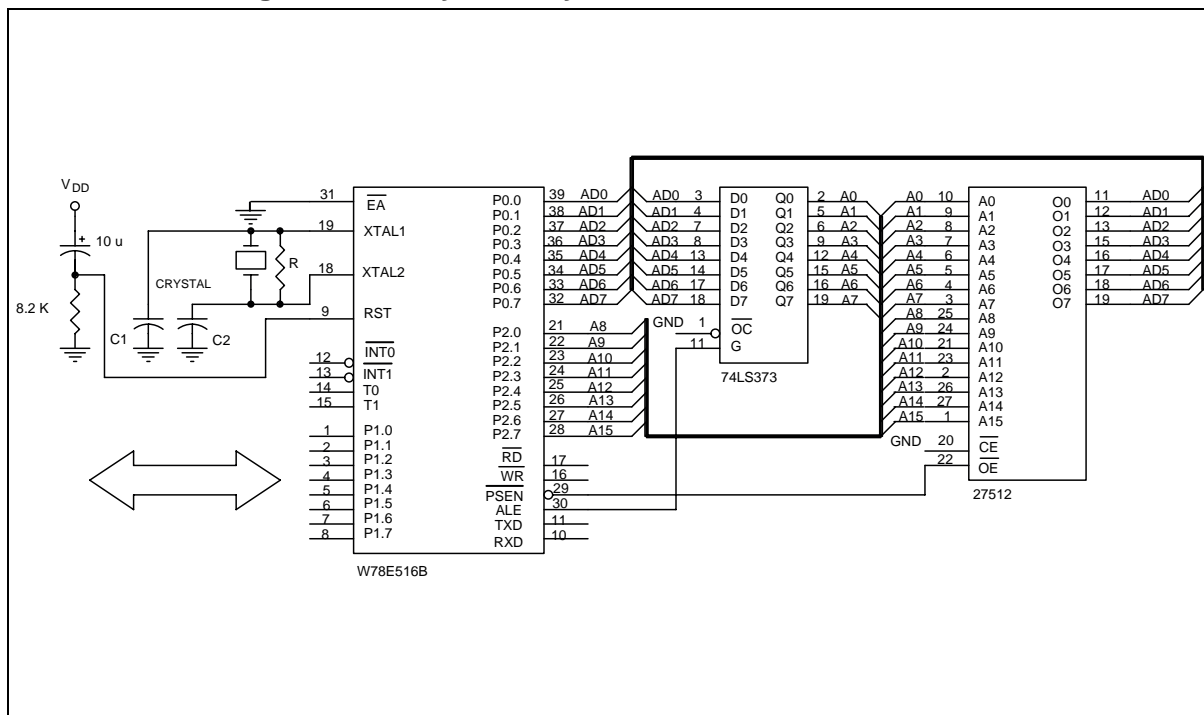


Figure A

CRYSTAL	C1	C2	R
6 MHz	47P	47P	-
16 MHz	30P	30P	-
24 MHz	15P	10P	-
32 MHz	10P	10P	6.8K
40 MHz	5P	5P	4.7K

Above table shows the reference values for crystal applications.

#### Notes:

1. C1, C2, R components refer to Figure A
2. Crystal layout must get close to XTAL1 and XTAL2 pins on user's application board.

## 9.2 Expanded External Data Memory and Oscillator

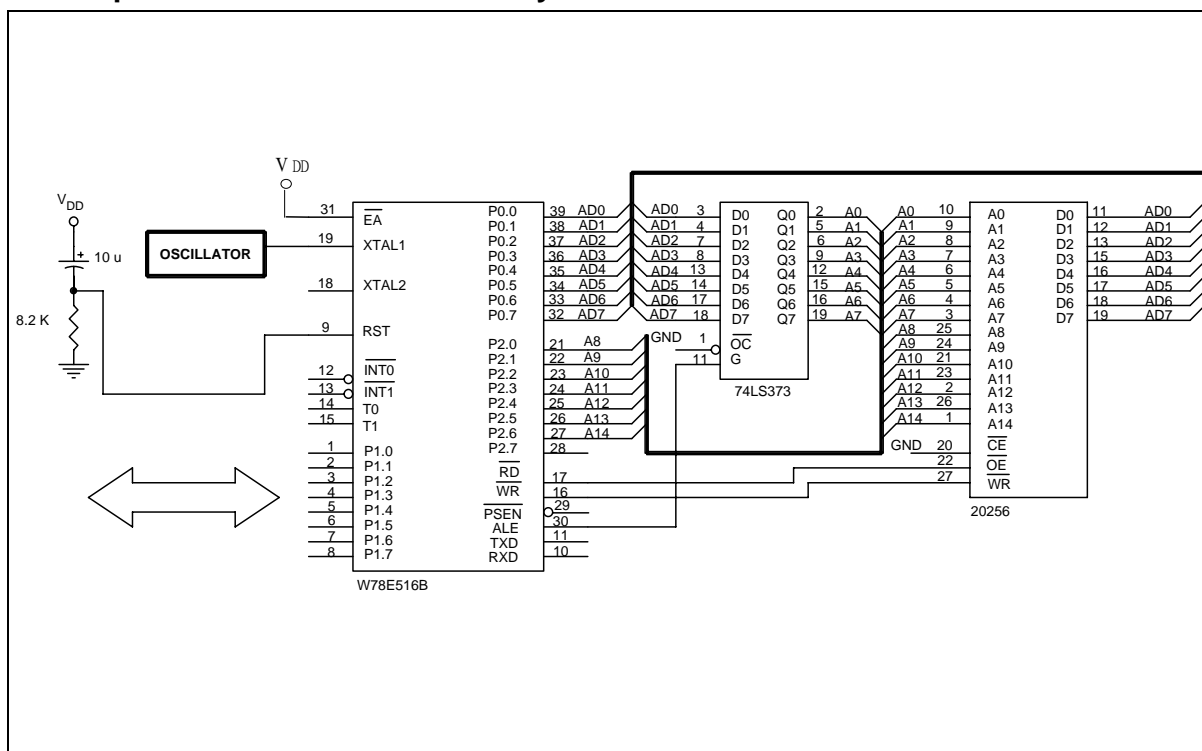
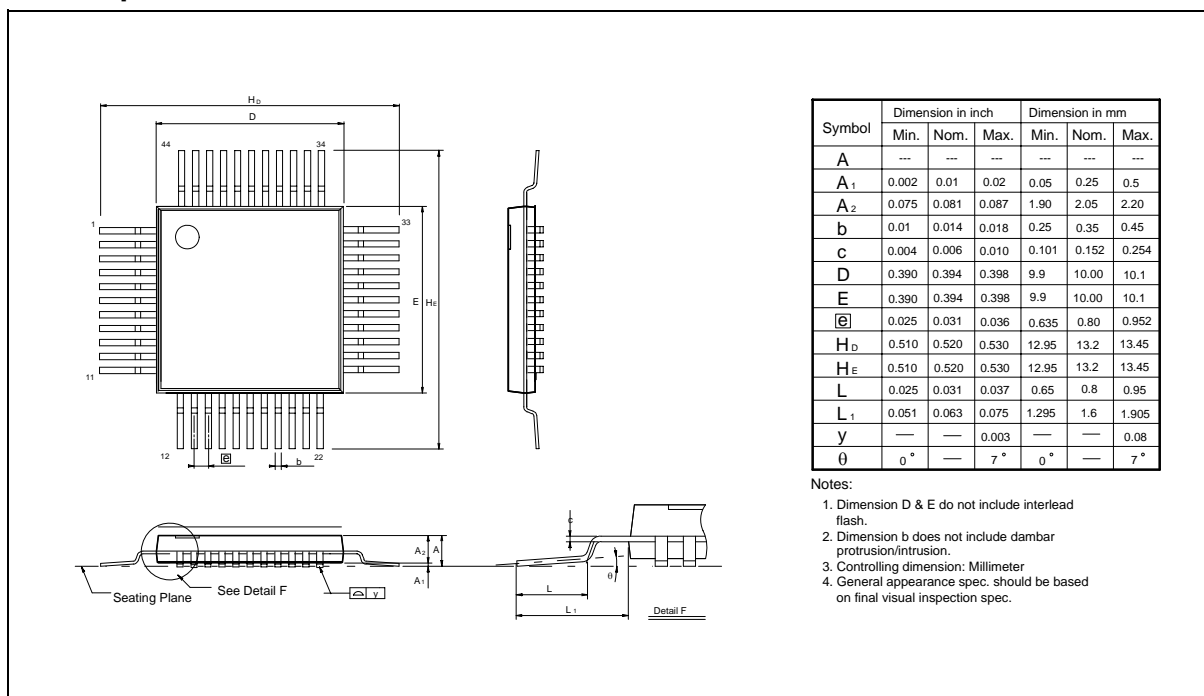


Figure B



Package Dimensions, continued.

### 10.3 44-pin PQFP





## MAIN\_4K:

```

MOV SP, #C0H      ; BE INITIAL SP REGISTER
MOV CHPENR, #87H   ; CHPENR = 87H, CHPCON WRITE ENABLE.
MOV CHPENR, #59H   ; CHPENR = 59H, CHPCON WRITE ENABLE.
MOV A, CHPCON
ANL A, #80H
CJNE A, #80H, UPDATE_64K ; CHECK F04KBOOT MODE ?

MOV CHPCON, #03H   ; CHPCON = 03H, ENABLE IN-SYSTEM PROGRAMMING.
MOV CHPENR, #00H   ; DISABLE CHPCON WRITE ATTRIBUTE

MOV TCON, #00H     ; TCON = 00H, TR = 0 TIMER0 STOP
MOV TMOD, #01H     ; TMOD = 01H, SET TIMER0 A 16BIT TIMER
MOV IP, #00H       ; IP = 00H
MOV IE, #82H       ; IE = 82H, TIMER0 INTERRUPT ENABLED
MOV R6, #F0H
MOV R7, #FFH
MOV TL0, R6
MOV TH0, R7
MOV TCON, #10H     ; TCON = 10H, TR0 = 1, GO
MOV PCON, #01H     ; ENTER IDLE MODE

```

## UPDATE\_64K:

```

MOV CHPENR, #00H   ; DISABLE CHPCON WRITE-ATTRIBUTE
MOV TCON, #00H     ; TCON = 00H, TR = 0 TIM0 STOP
MOV IP, #00H       ; IP = 00H
MOV IE, #82H       ; IE = 82H, TIMER0 INTERRUPT ENABLED
MOV TMOD, #01H     ; TMOD = 01H, MODE1
MOV R6, #3CH       ; SET WAKE-UP TIME FOR ERASE OPERATION, ABOUT 15 mS. DEPENDING
                   ; ON USER'S SYSTEM CLOCK RATE.

MOV R7, #B0H
MOV TL0, R6
MOV TH0, R7

```

## ERASE\_P\_4K:

```

MOV SFRCN, #22H    ; SFRCN(C7H) = 22H ERASE 64K
MOV TCON, #10H     ; TCON = 10H, TR0 = 1, GO
MOV PCON, #01H     ; ENTER IDLE MODE (FOR ERASE OPERATION)

```

```

;*****
;

```

## ;\* BLANK CHECK

```

;*****
;

```

```

MOV SFRCN, #0H     ; READ 64KB APROM MODE
MOV SFRAH, #0H     ; START ADDRESS = 0H
MOV SFRAL, #0H
MOV R6, #FBH       ; SET TIMER FOR READ OPERATION, ABOUT 1.5 μS.
MOV R7, #FFH
MOV TL0, R6
MOV TH0, R7

```

## BLANK\_CHECK\_LOOP:

```

SETB TR0           ; ENABLE TIMER 0
MOV PCON, #01H     ; ENTER IDLE MODE
MOV A, SFRFD       ; READ ONE BYTE
CJNE A, #FFH, BLANK_CHECK_ERROR

```



```

INC SFRAL          ; NEXT ADDRESS
MOV A, SFRAL
JNZ BLANK_CHECK_LOOP
INC SFRAH
MOV A, SFRAH
CJNE A, #0H, BLANK_CHECK_LOOP ; END ADDRESS = FFFFH
JMP PROGRAM_64KROM

```

BLANK\_CHECK\_ERROR:

```

MOV P1, #F0H
MOV P3, #F0H
JMP $

```

```

;*****
;
; * RE-PROGRAMMING 64KB APROM BANK
;*****
;

```

PROGRAM\_64KROM:

```

MOV DPTR, #0H      ; THE ADDRESS OF NEW ROM CODE
MOV R2, #00H       ; TARGET LOW BYTE ADDRESS
MOV R1, #00H       ; TARGET HIGH BYTE ADDRESS
MOV DPTR, #0H      ; EXTERNAL SRAM BUFFER ADDRESS
MOV SFRAH, R1       ; SFRAH, TARGET HIGH ADDRESS
MOV SFRCN, #21H     ; SFRCN (C7H) = 21 (PROGRAM 64K)
MOV R6, #5AH        ; SET TIMER FOR PROGRAMMING, ABOUT 50 μS.
MOV R7, #FFH
MOV TL0, R6
MOV TH0, R7

```

PROG\_D\_64K:

```

MOV SFRAL, R2       ; SFRAL (C4H) = LOW BYTE ADDRESS
MOVX A, @DPTR       ; READ DATA FROM EXTERNAL SRAM BUFFER
MOV SFRFD, A        ; SFRFD (C6H) = DATA IN
MOV TCON, #10H      ; TCON = 10H, TR0 = 1, GO
MOV PCON, #01H      ; ENTER IDLE MODE (PRORGAMMING)
INC DPTR
INC R2
CJNE R2, #0H, PROG_D_64K
INC R1
MOV SFRAH, R1
CJNE R1, #0H, PROG_D_64K

```

```

;*****
;
; * VERIFY 64KB APROM BANK
;*****
;

```

```

MOV R4, #03H        ; ERROR COUNTER
MOV R6, #FBH        ; SET TIMER FOR READ VERIFY, ABOUT 1.5 μS.
MOV R7, #FFH
MOV TL0, R6
MOV TH0, R7
MOV DPTR, #0H       ; The start address of sample code
MOV R2, #0H         ; Target low byte address
MOV R1, #0H         ; Target high byte address
MOV SFRAH, R1       ; SFRAH, Target high address
MOV SFRCN, #00H     ; SFRCN = 00 (Read ROM CODE)

```



## 12. REVISION HISTORY

VERSION	DATE	PAGE	DESCRIPTION
A5	June, 2002	-	Formerly issued
A6	June, 2004	3	Revise part number in the item of packages
A7	Aug, 2004	26	Revise title of 10.1
A8	Jan, 2005	3	Add Lead Free package
A9	April 20, 2005	35	Add Important Notice
A10	October 2, 2006		Remove block diagram
A11	December 4, 2006	3	Remove all Leaded package parts

### Important Notice

Winbond products are not designed, intended, authorized or warranted for use as components in systems or equipment intended for surgical implantation, atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, or for other applications intended to support or sustain life. Further more, Winbond products are not intended for applications wherein failure of Winbond products could result or lead to a situation wherein personal injury, death or severe property or environmental damage could occur.

Winbond customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Winbond for any damages resulting from such improper use or sales.

---

Please note that all data and specifications are subject to change without notice.  
All the trademarks of products and companies mentioned in this datasheet belong to their respective owners.